

N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY

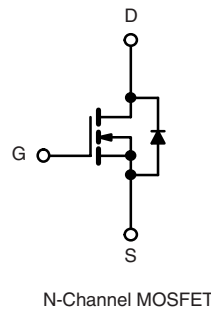
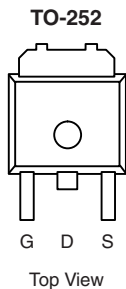
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^a	Q_g (Typ.)
30	0.0033 at $V_{GS} = 10$ V	80	32 nC
	0.0045 at $V_{GS} = 4.5$ V		

FEATURES

- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested
- PWM Optimized

APPLICATIONS

- LCD Display Backlight Inverters
- DC/DC Converters


RoHS
 COMPLIANT


ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150^\circ\text{C}$)	I_D	$T_C = 25^\circ\text{C}$	A
		$T_C = 70^\circ\text{C}$	
		$T_A = 25^\circ\text{C}$	
		$T_A = 70^\circ\text{C}$	
Pulsed Drain Current	I_{DM}	320	A
Continuous Source-Drain Diode Current	I_S	$T_C = 25^\circ\text{C}$	
		$T_A = 25^\circ\text{C}$	
Single Pulse Avalanche Current	I_{AS}	70	
Avalanche Energy	E_{AS}	166	mJ
Maximum Power Dissipation	P_D	$T_C = 25^\circ\text{C}$	W
		$T_C = 70^\circ\text{C}$	
		$T_A = 25^\circ\text{C}$	
		$T_A = 70^\circ\text{C}$	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^b	R_{thJA}	15	20	$^\circ\text{C/W}$
Maximum Junction-to-Case	R_{thJC}	1.1	1.6	

Notes:

a. Package limited.

b. Surface mounted on 1" x 1" FR4 board.

SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	30			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 1.0 mA		44		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			- 5.9		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1		3.0	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 24 V, V _{GS} = 0 V			1	μA
		V _{DS} = 24 V, V _{GS} = 0 V, T _J = 70 °C			20	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	80			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 20 A		0.0033	0.0045	Ω
		V _{GS} = 4.5 V, I _D = 15 A		0.0045	0.0078	
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 15 A		85		S
Dynamic ^b						
Input Capacitance	C _{iSS}	V _{DS} = 24 V, V _{GS} = 0 V, f = 1 MHz		4050		pF
Output Capacitance	C _{oss}			377		
Reverse Transfer Capacitance	C _{rSS}			92		
Total Gate Charge	Q _g	V _{DS} = 24 V, V _{GS} = 10 V, I _D = 20 A		36		nC
		V _{DS} = 24 V, V _{GS} = 4.5 V, I _D = 20 A		19		
Gate-Source Charge	Q _{gs}			6.3		
Gate-Drain Charge	Q _{gd}			4.8		
Gate Resistance	R _g	f = 1 MHz		2.5		Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = 24 V, R _L = 1 Ω I _D ≅ 20 A, V _{GEN} = 4.5 V, R _g = 1 Ω		38		ns
Rise Time	t _r			15		
Turn-Off Delay Time	t _{d(off)}			52		
Fall Time	t _f			12		
Turn-On Delay Time	t _{d(on)}	V _{DD} = 24 V, R _L = 1 Ω I _D ≅ 20 A, V _{GEN} = 10 V, R _g = 1 Ω		13		
Rise Time	t _r			7		
Turn-Off Delay Time	t _{d(off)}			30		
Fall Time	t _f			8		
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			80	A
Pulse Diode Forward Current ^a	I _{SM}				320	
Body Diode Voltage	V _{SD}	I _S = 10 A		0.7	1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 20 A, dI/dt = 100 A/μs, T _J = 25 °C		29		ns
Body Diode Reverse Recovery Charge	Q _{rr}			16		nC
Reverse Recovery Fall Time	t _a			13		ns
Reverse Recovery Rise Time	t _b			11		

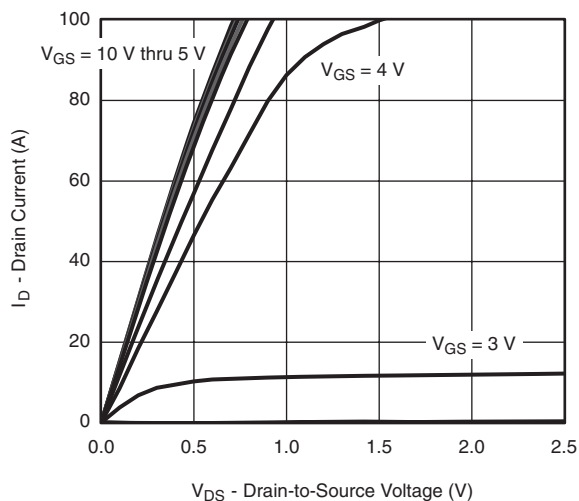
Notes:

 a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

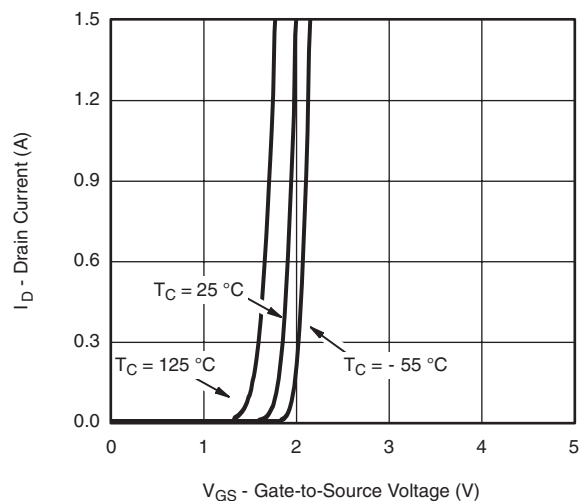
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

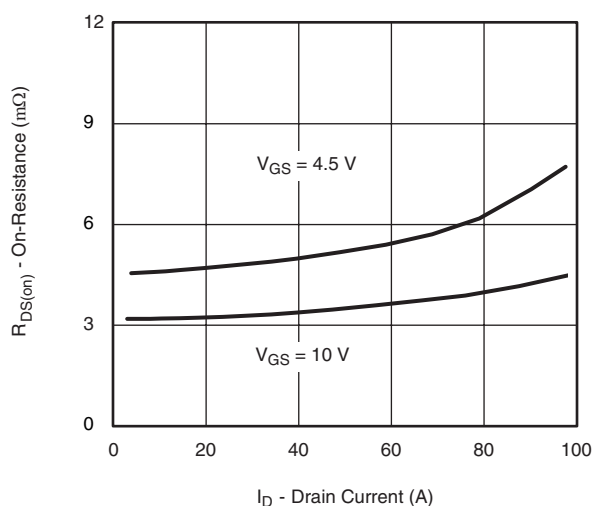
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



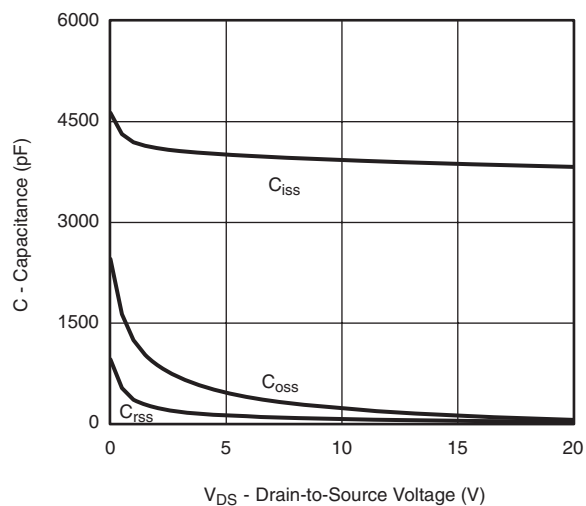
Output Characteristics



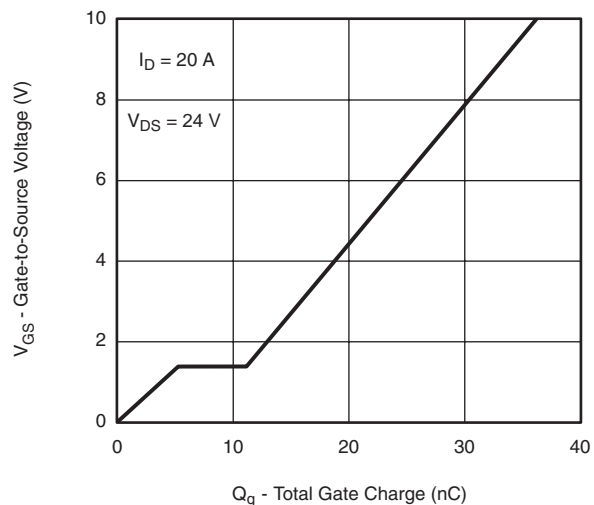
Transfer Characteristics



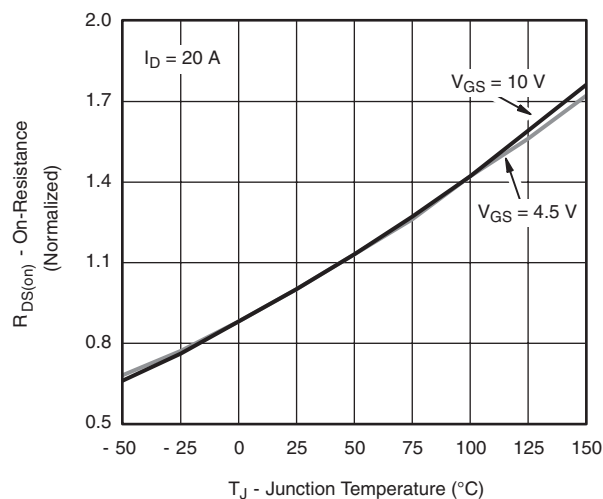
On-Resistance vs. Drain Current



Capacitance

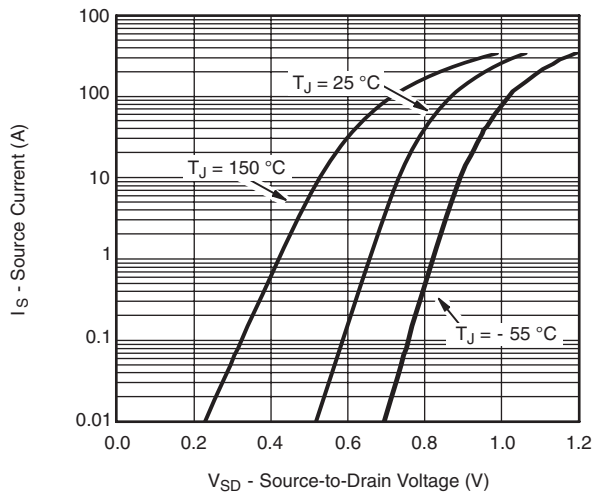


Gate Charge

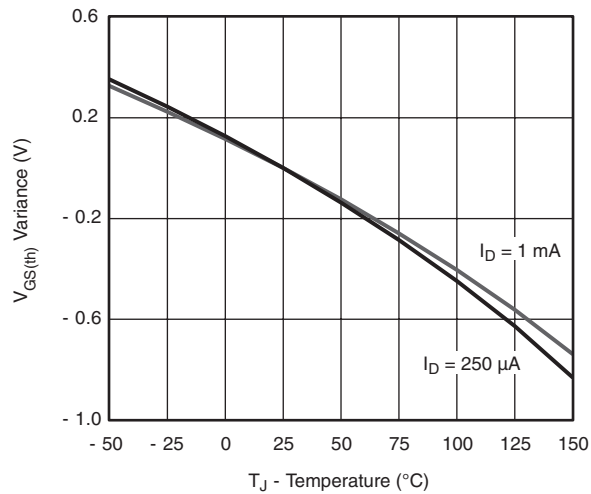


On-Resistance vs. Junction Temperature

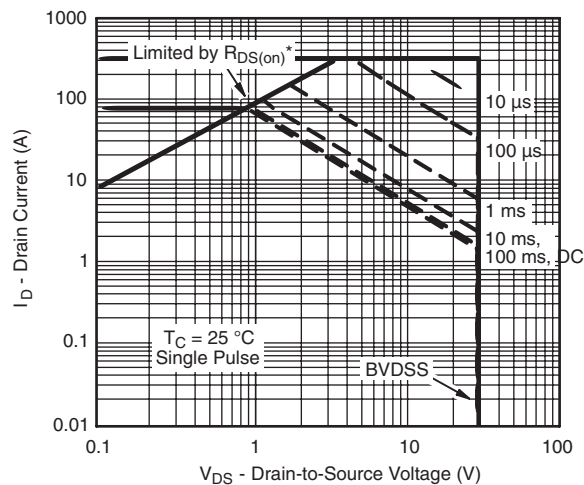
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



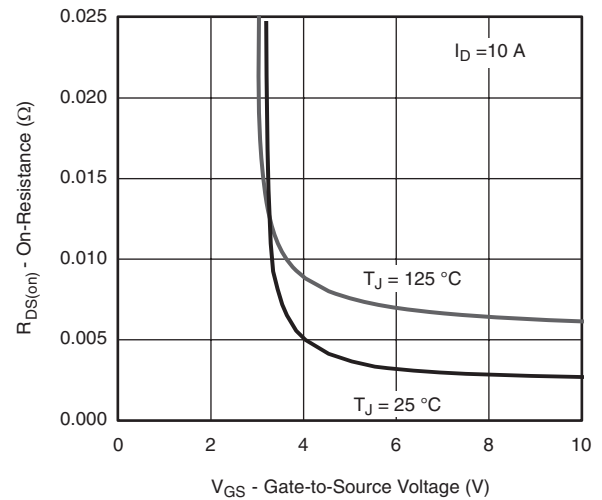
Source-Drain Diode Forward Voltage



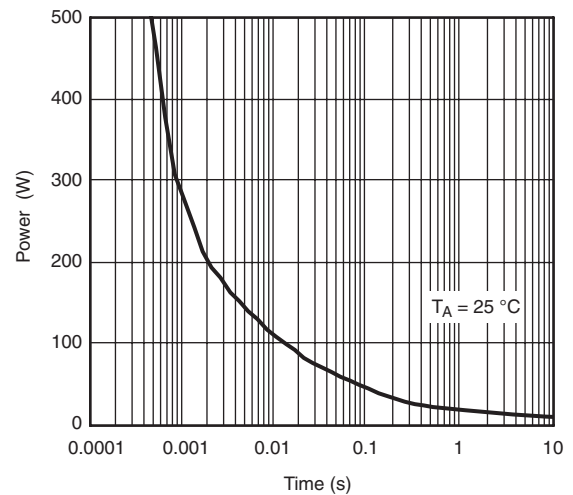
Threshold Voltage



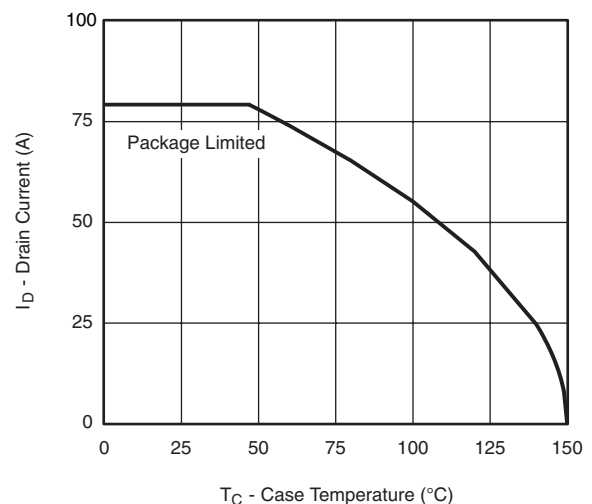
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified
Safe Operating Area, Junction-to-Case



On-Resistance vs. Gate-to-Source Voltage

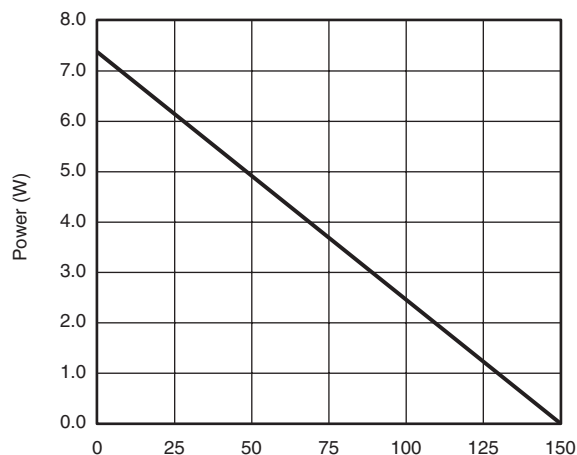


Single Pulse, Junction-to-Ambient

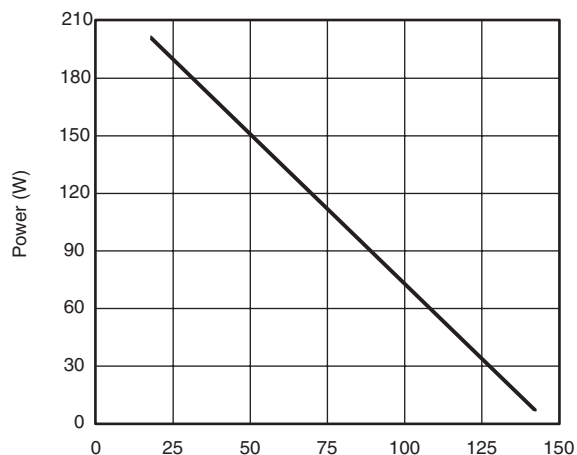


Current Derating*, Junction-to-Case

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



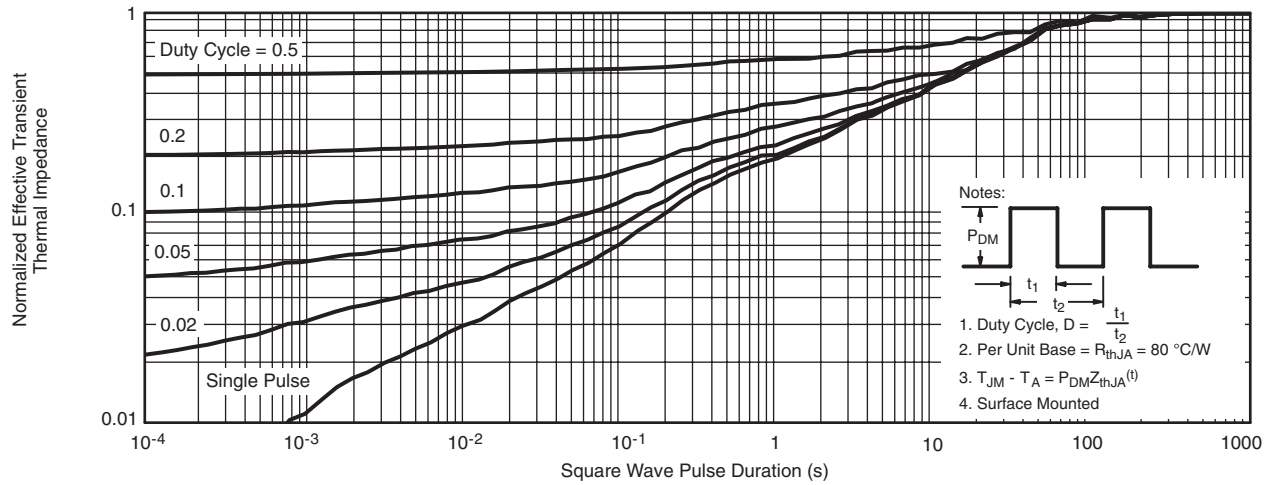
T_J - Junction Temperature (°C)
Power Derating, Junction-to-Ambient



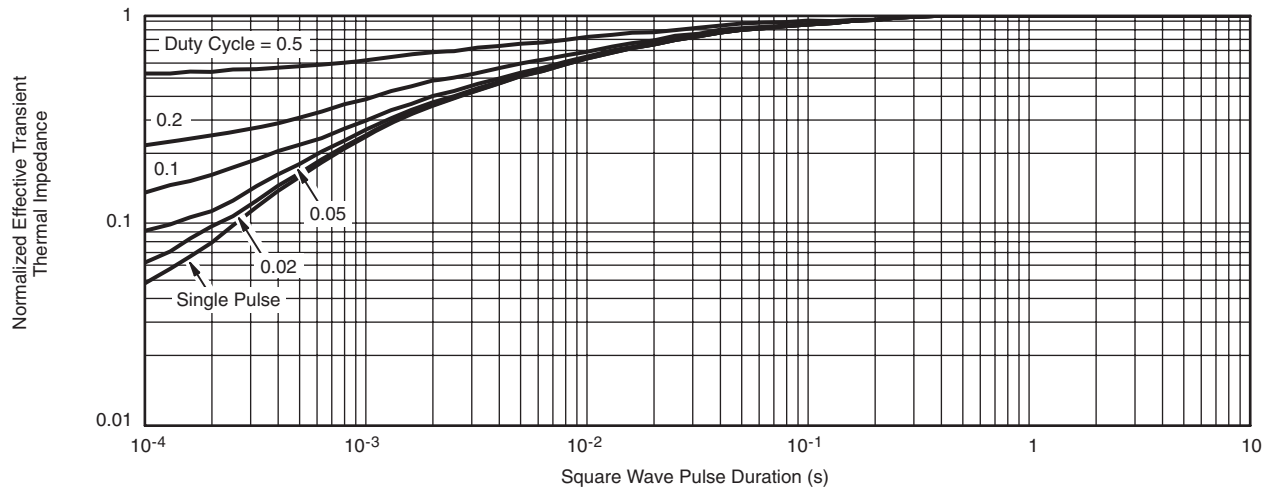
T_J - Junction Temperature (°C)
Power Derating, Junction-to-Case

* The power dissipation P_D is based on $T_{J(max)} = 150\text{ }^{\circ}\text{C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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